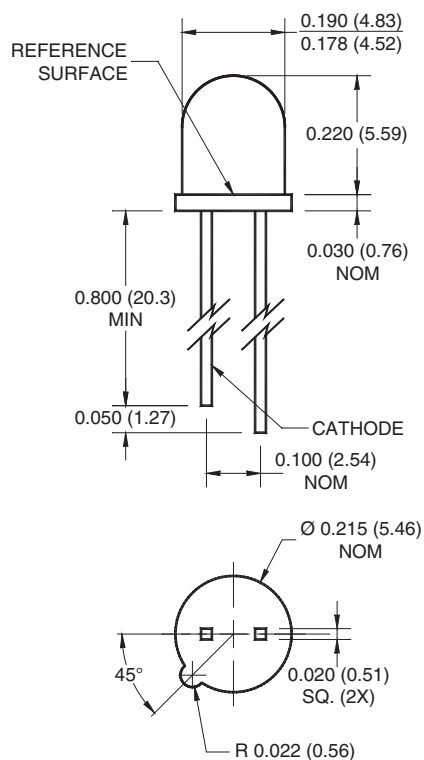


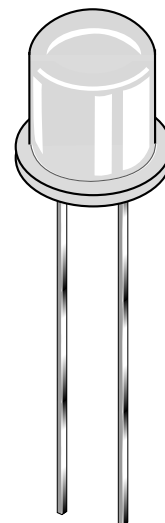
QED522 QED523

PACKAGE DIMENSIONS

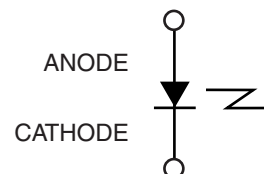


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The QED522/523 is an 880 nm AlGaAs LED encapsulated in a clear, peach tinted, plastic TO-46 package.

FEATURES

- $\lambda = 880$ nm
- Chip material = AlGaAs
- Package type: Plastic TO-46
- Matched Photosensor: QSD722/723/724
- Narrow Emission Angle, 20°
- High Output Power
- Package material and color: clear, peach tinted, plastic

QED522 QED523

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T_{OPR}	-40 to + 100	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 to + 100	$^\circ\text{C}$
Soldering Temperature (Iron) ^(2,3,4)	T_{SOL-I}	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) ^(2,3)	T_{SOL-F}	260 for 10 sec	$^\circ\text{C}$
Continuous Forward Current	I_F	100	mA
Reverse Voltage	V_R	5	V
Power Dissipation ⁽¹⁾	P_D	200	mW

NOTES:

1. Derate power dissipation linearly 2.67 mW/ $^\circ\text{C}$ above 25°C .
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
Peak Emission Wavelength	$I_F = 100\text{ mA}$	λ_{PE}	—	880	—	nm
Emission Angle	$I_F = 100\text{ mA}$	$2\theta_{1/2}$	—	20	—	Deg.
Forward Voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F	—	—	1.8	V
Reverse Current	$V_R = 5\text{ V}$	I_R	—	—	10	μA
Radiant Intensity QEC522	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_E	20	—	80	mW/sr
Radiant Intensity QEC523	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_E	40	—	—	mW/sr
Rise Time	$I_F = 100\text{ mA}$	t_r	—	800	—	ns
Fall Time		t_f	—	800	—	ns

Fig. 1 Normalized Radiant Intensity vs. Forward Current

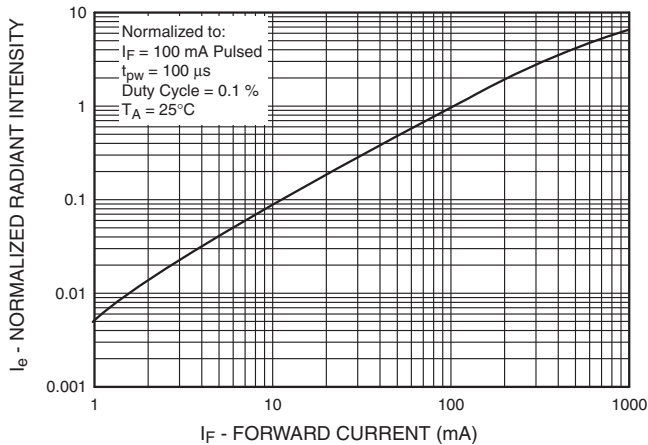


Fig. 2 Forward Voltage vs. Ambient Temperature

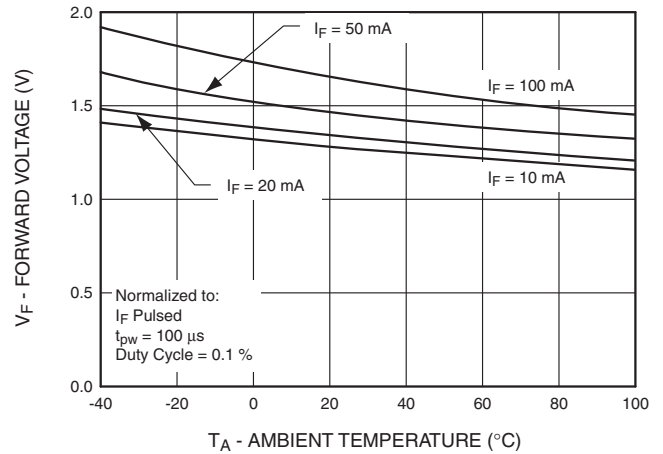


Fig. 3 Normalized Radiant Intensity vs. Wavelength

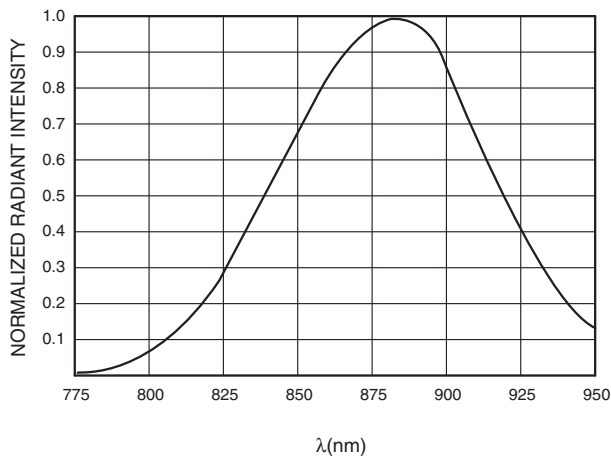
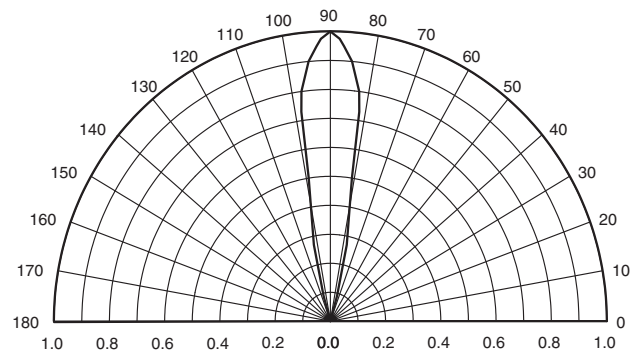


Fig. 4 Radiation Diagram



DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.